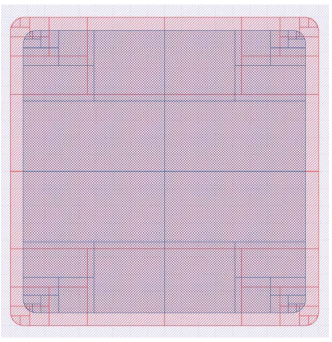
LMESD36022

CHIP APPEARANCE



PIN CONFIGURATION

FEATURES

- 1-Channel Uni-directional ESD diode
- Operating Voltage: 36V
- Ultra Low Leakage: nA Level
- Response time is typically < 10 ns
- RoHS compliant
- Ultra Small Die Size, suitable for DFN1006 or DFN0603 package
- IEC6100-4-2(ESD)： +/-20KV(Air) +/-20KV(Contact)

WAFER INFORMATION

ITEM	CHARACTERISTICS
Wafer size	8Inch (200mm)
Chip size(include 40um scribe)	220umx220um
Pad size	180umx180um
Wafer thickness	150±10um
Gross Die (3mm edge clearance)	600,000dies wafer
Top Metallization	AlSiCu:4.5um
Back Metallization	Ti/Ni/Ag

ABSOLUTE MAXIMUM RATINGS(TA=25℃ UNLESS OTHERWISE SPECIFIED)

Parameter	Symbol	Value	Uinits
Peak Pulse Power (8/20μs)	P_{pk}	50	W
ESD per IEC61000-4-2 (Air) ESD per IEC61000-4-2 (Contact)	V_{ESD}	±20 ±20	kV
Operating Temperature Range	T_J	-55 to +150	℃
Storage Temperature Range	T_{stg}	-55 to +150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

Parameter	Symbol	Condition	Min	Typ	Max	Units
\Reverse Stand-off Voltage	VRWM				36	V
Reverse Breakdown Voltage	VBR	It=1mA	39	43	44.5	V
Reverse Leakage Current	IR	VRWM=36V			0.2	uA
Clamping Voltage	VC	Ipp=1A,tp=8/20us			55	V
Junction Capacitance	Cj	VR=0V,f=1MHz		8		pF

Matters Attention:

1 、 Chip storage conditions(recommended)：nitrogen protection，Temperature 25±5℃ Humidity≤45%；

2、 When packaging，please remove the core within 3mm from the edge of the circle；